Chapter 15

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Interface Engineering and Stability of Graphene-Based Devices

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ABSTRACT

In this chapter, a complete description of the bulk characteristics of graphene as well as why the interface engineering plays an essential role in improving its characteristics in various applications is presented. The chapter starts with the description of unusually high electronic, mechanical, and thermal properties of graphene, and then differentiates among multiple representations and types of graphene, such monolayer, bilayer, graphene oxide (GO), and reduced graphene oxide (rGO). Common interface types: metal-graphene, dielectric-graphene, and polymer-graphene are studies with special focus on their effects on device behavior. The chapter discusses more complex interface engineering methods to maximize interfacial contact, carrier transport and material compatibility. The stability of graphene-metal and graphene-dielectric interfaces, and functional integration of graphene with polymers and organic materials are the detailed areas. Applications that are emerging as important where control of the interface is desirable include energy storage and conversion devices, graphene-based quantum systems and integration with CMOS technology. With the introduction of theoretical understanding and practical knowledge, this chapter will be a resourceful piece of work to both researchers and engineers who could tailor their interests to maximize the use of graphene in the next generation technologies.

Keywords: Graphene; Interface Engineering; Graphene Oxide (GO); Reduced Graphene Oxide (rGO); Graphene–Metal Contact; Dielectric Stability; Polymer Composites; Energy Storage; Supercapacitors; Quantum Devices; CMOS Integration; Charge Transport; Surface Functionalization; Two-Dimensional Materials; Nanotechnology.

INTRODUCTION

There has been great interest concerning Graphene based gadgets owing to the impressive physical and chemical characteristics of graphene, such as high electron transportability, mechanical durability, and thermal conductivity. Nevertheless, the effectiveness and stability of performance of these devices critically relies upon the NBC of their interfacial interactions with metals, dielectrics, and polymers. Interface engineering has come up as one of the most essential options to maximize charge transport, adhesion, and chemical compatibility in composite devices frameworks. By controlling the interfacial phenomena, it becomes possible to integrate graphene onto existing semiconductor platforms and to make graphene more appropriate to energy storage, quantum electronics and flexible technologies. This chapter has investigated

the basic ideas and new methods in engineering and stabilizing graphene-interface to liberate all their technological potential. Devices made of graphene are also getting more attention as it has most possibilities in other fields such as sensors, memory, solar cell and so on. One of their highlights in performance is greatly hinged on how their engineering of interfaces and the accrued stabilizing management within their performance can help as a determining factor towards its reliability and effectiveness. The share of recent researches and findings in this discussion includes many attempts to promote the continuation of the stability of devices based on graphene with the help of all possible innovations and methods of interface engineering. It is notable about the monolayer graphene that it has a very low thickness that makes it able to respond and recover within a short period, particularly in applications that involve humidity detection. Gao et al. emphasize that device using monolayer graphene enjoy the advantage of atomic structure so that their sensor responses are very fast. They remark as well that devices that use double-layer graphene also encounter problems because the bottom layer performance may be impaired by the underlying layer of SiO2 substrate since their hydrophilicities may differ hence demonstrating a fundamental problem of interface engineering.[1] Interfacial properties can play an important role in influencing the performance and thus, there is a need to design specific engineering approaches to make the device functionalities better. The process of defect engineering becomes an important tool in enhancing interface stability and the performance of overall device, in graphene applications. The experiment conducted by Kim et al.[2] reveals that the carrier mobility can increase by about 230,8 percent in the case of selective defect healing of graphene electrodes, which would mean a major advance in the electric properties. Based on their study they postulated that healing of the defects affects the Schottky barrier at the graphene/Tungsten diselenide (WSe2) interface, which added to the long-term stability. The type of such findings highlights the necessity of developing the knowledge and control of the defects at the atomic scale to increase the functionality and reliability of the graphene-based devices.

In addition, interfaces between graphene and other 2D materials bear new ways to interface manipulation that can be used to improve performance. Agarwal et al.[3] address the prospects of integrating graphene and hexagonal boron nitride (hBN) to produce electro-absorption modulators that have a higher efficiency of modulation and thermal stability. The vertical integration strategy also points at the necessity of accurate control over the interface interactions to obtain synergistic effect in device performance. Graphene-based materials have an ideal balance of strength and ductility that is critical in applications of application where mechanical robustness is considered. Manna et al.[4] introduce a new method of using amino acid modified wrinkled graphene oxide in memory operations establishing the long-range stability of the resistive memory structures. Their results also underline the significance of chemical modifications to the long-term performance of any graphene-based devices as well as improving both the lifetime and reliability of the latter. Graphene is a critical area of research and should be encased in composites to increase their durability. According to Lin et al.[5], the stable electrochemical energy storage based on dense reduced graphene oxide films has overcome the stacking tendency of the graphene sheets that has always been a problem when maintaining high storage capacity. Innovations in the material design are able to result in more functional and stable energy storage systems by paying attention to good mechanical stability and ion diffusion properties.

Lastly, Razaq et al.[6] review relates to remote developments in graphene-based materials in charge transfer efficiency in PSCs in which the authors have discussed the role of interface engineering in achieving high performance and device stability, which is also of dual importance. Their results are an indication that there is a push within the research community to meet the

electronic properties as well as stability using composite and interface engineering. As a final conclusion, the study of graphene-based devices is developing at a high rate and with the synergistic success in engineering the interface and with the increased development of stability principles. Ongoing research portends both novelty and complexity in what graphene might do to advance devices, whether sensors and memory, energy systems and optoelectronics. With this growing body of knowledge in how things go on at such delicate interfaces, we can also count on coming up more super-sophisticated and stable graphene-based technologies.

Fundamentals of Graphene and Its Interfaces

Electronic, mechanical, and thermal properties of graphene

The unique physical characteristics of graphene are still based on the fact that this material is two-dimensional and consists of sp2-hybridized carbon atoms assembled in the shape of a honeycomb lattice. Electrically it exhibits high carrier mobility and ballistic conduction. The mechanical properties of graphene are rather large: its Young modulus is ~1 TPa and it is naturally strong with a strength of 130 GPa. Its conductivity is more than 3000 W/mK thermally. Graphene which is a one-atom thick sheet of carbon atoms located in a two-dimensional honeycomb structure, has received exceptional interest because of its unusual electronic, mechanical, and thermal signs. Its distinctive composition does not only make it an extraordinarily conductive and strong material but also makes it one that is to be an important development in future technology in many diverse areas, such as electronics and materials science. The present synthesis presents the multidimensional nature of graphene, outlining its electronic, mechanical, and thermal properties, and it relies on the variety of recent academic sources (figure 1). Carbon nanotubes (CNTs) properties in the thermal and electrical aspects were studied greatly to analyze heat flow and charge transport in graphene-like nano structures. Presence of rare-earth dopant such as gadolinium also has a pronounced effect on thermal conductivity and electron scattering in both CNTs and GO. The research will be vital in the understanding of the intrinsic material behavior of carbon-based nanomaterials in the future electronic and energy systems.[7,8,9,10,11,12] Electrical properties of the graphene are of special interest, they are characterized by high electron mobility which enables exceptional use as next generation transistor and other electronic components. Measurings of suspended graphene samples indicate electronic mobilities as high as 200 000 cm 2 /V s, which is way more than what ordinary silicon substrates show.[13] Graphene can also transfer the charges in an efficient way since it has a small electronic band gap, a property essential to applications in high-speed electronics and optoelectronic devices.

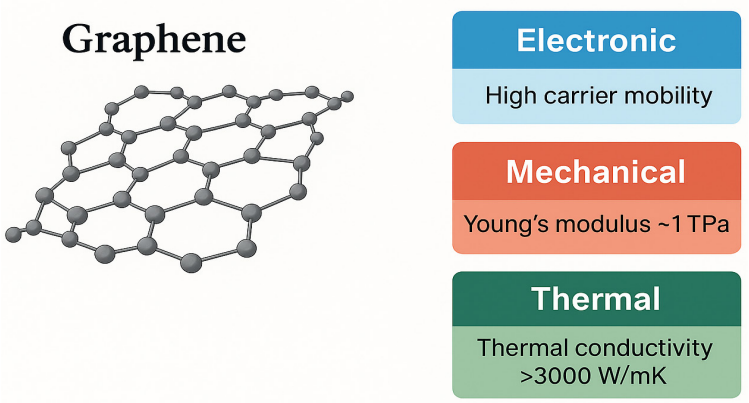

Figure 1. Electronic, mechanical, and thermal properties of graphene

Moreover, the combination of diverse materials, including gallium nitride (GaN), will provide an opportunity to create heterostructures that will capitalize on the strengths of both materials and, as a result, improve performance parameters of power sources and photonic applications.[14]

Mechanical characteristics of graphene are also revolutionary in parallel with its electronic properties. It is considered to be one of the most robust materials and its tensile strength can reach up to around 130 Gigapascals and stretching capacity is intrinsic to an extent that great deformations can be achieved without failing. This strength is exuberant because of the two-dimensionality which makes strong covalent bonds using sp2 hybridized carbon atoms. But the structural integrity may be affected by a number of factors such as existence of defects and the size of the graphene film. It is also known that mechanical characteristics of the suspended graphene may be degraded with increasing diameter caused by accumulated defects and associated influence of surface tension during preparation conditions that can cause premature failure and crack.[15] Moreover, the orientation and dispersion of graphene in the composition of material also have a significant effect on their overall mechanical effectiveness where, due to correct dispersion, it is possible to enhance the interfacial adhesion and strength.[16] In addition to being electrical and mechanical, graphene is a very accomplished thermal conductor. Research has proved that graphene thermal conductivity is more than 5000 W/m-K which makes it an exemplary heat dissipation product in electronic appliances.[17] This mix of properties is unique and makes graphene an invaluable asset to engineering of higher fidelity thermal interface materials thereby extending its possible use to the high temperature electronics field. To sum up, a graphene is one of the materials of unprecedented potential because of its unprecedented electronic, mechanical and thermal characteristics. Further research into the nature of its behavior and its possible applications are being driven by interdisciplinary research directions and current research is attempting to streamline its usefulness in a number of technology fields. The potential of grape to be used in electronic devices, its ability to be incredibly strong and thermally manageable, indicates that the material will still be used in the technological change as in the future, it will improve the performance and provide efficiencies in a vast number of applications.

Types of graphene: monolayer, bilayer, reduced graphene oxide (rGO), graphene oxide (GO)

The monolayer graphene is composed of one layer of carbon atoms contacting in 2-dimensional (2D) honeycomb lattice, providing outclass electron mobility and mechanical vulnerability. The bilayer graphene consists of two stacked sheets of graphene sheets which are commonly in an AB (Bernal) stacking structure, and which changes its electronic band structure, and provides pathways to tunable bandgaps under an electric field.

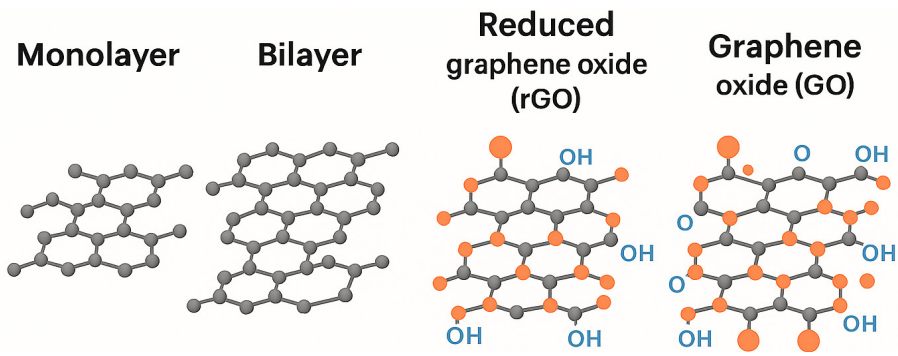

Figure 2. Types of Graphene: Monolayer, Bilayer, rGO, and GO

The interlayer interaction between the layers of bilayer graphene presents new quantum physics, which is appealing towards future nanoelectronics applications. Graphene oxide (GO) is a highly oxidized version of graphene that has oxidized functional groups (hydroxyl, carboxyl, and epoxy) and has a hydrophilic nature and is soluble in water. GO is electrically less conductive because of a broken sp2 lattice structure but the mechanical and chemical versatility of the structure remains very useful in functionalization processes (figure 2).

During thermal, chemical or electrochemical reduction, a portion of the electron-withdrawing oxygen groups are removed as reduced graphene oxide (rGO) regains partial electrical conductivity and conjugation. Though rGO may not restore the initial structure of graphene fully, it provides a trade-off between conductivity and chemical reactivity in fine senses, so it can be applied to energy storage and sensor tasks. The electronic properties of monolayer and bilayer graphene differ; one can thus make a choice that depends on which properties one needs in a transistor or quantum device. GO and rGO have high applications in composite material, flexible electronics, and biomedical platform as the surface chemistry is processable and can be adjusted. Both types of graphene have unique advantages relative to each other regarding the application and hence caution is important in terms of its synthesis and integration. Graphene oxide (GO) and then reduced graphene oxide (rGO) was prepared and properties of its layers were studied with respect to structural, optical and electrical properties. Such types of graphene provide adjustable bandgaps and chemical activity, missing in the monolayer and bilayer graphene. Their application is backed by the studies on transparent electronics and flexible devices.[18,19,20,21] Two-dimensional (2D) graphene is an allotrope of carbon with an atomically thin sheet of carbon as the fundamental unit. Graphene allotrope has a variety of forms, such as monolayer graphene, bilayer graphene, graphene oxide (GO) and reduced graphene oxide (rGO). Each of them has its own characteristic structural and functional properties that allow broad range of application in fields including materials science, electronics and energy storage. This comparative analysis of the various types of graphene uses the modern advancements related to them in order to explain their unique properties and possible uses. The physical properties of monolayer graphene are the properties of a single sheet of carbon atoms in honeycomb lattice. This structure gives the material impressive mechanical, thermal, and electrical characteristics and thus one of the most studied materials over the past years. Monolayer graphene is frequently produced by the chemical vapor deposition (CVD) method on copper substrates; it has been demonstrated that over nucleation density of 30 mm 2 1 results in domains that are monolayer with around 2500 of a lateral dimension.[22] Conversely, bilayer graphene is composed with two layers of graphene, and different stacking patterns such as very rare AB stacking, and AA stacking. The difference between these configurations has a great impact on the electronic behaviour of bilayer graphene. As an example, a bilayer graphene and stacking AB exhibit an optical and magneto-optical effect due to the parabolic dispersion relationship.[23] Another graphene derivative is graphene oxide (GO) that contains oxygen-bearing functional groups, changing significantly its properties in comparison with pristine graphene. GO is normally produced through the oxidation process of graphite; the oxidation is done through processes like the method of Hummer (a process that makes it easy to add polar groups). The generated hydrophilicity of GO allows its dispersing in watery conditions with broader uses of GO in coatings, membranes, and composites.[24] All the varied usages of reduced graphene oxide lie in its specific electrical conductivity and quantity of functional groups, which allow rGO to exhibit characteristics with a markedly better performance in energy-storing applications, including lead-acid batteries, where it serves as a conductive additive to increase the charge-discharge performance.[25] The diversity of these variations of graphene, such as monolayer, bilayer, GO, and rGO, demonstrates the vast opportunities that they provide in the future

technologies. The electronic properties of monolayer graphene and the bandgap of bilayer graphene are unique and the functional versatilities of GO and rGO emphasize the complexity of these materials. With research still unraveling novel ways of synthesis and employments, the contribution of graphene in all its forms is even more likely going to take a critical place in the future of materials science and material engineering. To sum it up, the varieties of graphene, monolayer graphene, bilayer graphene, GO, and rGO, have rather different peculiarities, which have made them applicable for a wide range of applications. The fact that such materials found the application in the emerging technologies, as well as high-speed electronics, advanced energy storage systems, further proves the transformative power of graphene in future innovations. Further studies on any of these forms of synthesis and their applications are bound to bring us closer to realizing and maximizing on the exceptional capabilities of graphene.

Common interface types: metal-graphene, dielectric-graphene, polymer-graphene

Interfaces between graphene, such as metal-, dielectric-, and polymer-graphene, is a system with a rich diversity of physical, chemical and electronic responses. All the types of interfaces have both their own benefits and limitations and these factors tend to decide the suitability of graphene in different areas of technology. These interfaces are important in the fields of electronics, energy storage and sensing and there is a high significance in understanding those interfaces in the advancement of materials in such fields. The nature of interaction between graphene and other materials plays a critical role towards the performance of graphene-based devices, especially at interface scale. Its research on metal and doped graphene oxide (GO) interface shows some interesting phenomena like negative different resistance (NDR) and charge transfer. The dielectric compatibilities are also mentioned in thin-film synthesis and in the electron paramagnetic resonance test study. As the research results indicate, interfacial qualities define the stability and performance of devices.[26,27,28]

The metals and graphene interfaces play an important role in electronic devices that use the metals as electrodes or contacts influencing the injection of the charges and the charge carrier mobility. The metal-graphene interfaces can be characterized by a high quality, which is determined by the work function of the metal, gating doping of the graphene and the geometrical shape of the contacts that determines the height of the Schottky barrier and the contact resistance.

FETs and capacitive devices the electric field across the graphene channel can be modified via dielectric layers, creating dielectric graphene interfaces. The common dielectrics used include SiO2, Al2O3 and h-BN but electronic performance in graphene may be degraded by rough surface, charge traps and phonon scattering. Atomic layer deposition (ALD) and self-assembled monolayers (SAMs) are the techniques of surface engineering such that the dielectric graphene interface is enhanced.

To begin with metal-graphene contacts, the contacts quality of these systems has a serious influence on the electronic characteristics of devices. The study conducted by Wang et al. emphasizes the phenomena of interfacial oxidation that occur when the metal is deposited on graphene and especially those metals that tend to oxidize (aluminum and titanium).[29] Oxides found at these metal-graphene interfaces have been demonstrated to affect the optical contrast which may in turn affect the transport properties of the carrier. The dynamics of these interfaces are well explained using techniques like the X-ray photoelectron spectroscopy and Raman spectroscopy and this demonstrates the sensitivity of this process towards the deposition conditions including the levels of background vacuum.[29] These results are important in the optimization of the manufacturing procedures of devices that use metal-graphene contacts.

Moreover, the role of electrostatics at graphene interfaces cannot be underestimated, particularly when one should consider a graphene-coated metal electrode within an electrolyte solution, which is explained by Saraf et al. Their study of the electrostatics also holds meaningful consequences in the employments such as super capacitors and in electrochemical sensors where the proposed interaction of the conducting graphene and the electrolyte is major factor to determine the effect of the devices. The authors underline the peculiarity of the interfaces due to their complexities in terms of metallic and non-metallic approaches to their study, which depends on the unique electrostatic response imposed by the specific nature of graphene.[30] This kind of knowledge will play an essential role in designing electrochemical systems since maximizing the graphene interface will improve the entire energy storage potential. Interactions between graphene interfaces using dielectrics are also ideas of high interest discussed by Loche et al.[31] The study outlines the role of the aqueous surfaces surface rigidity and metallicity on the dielectric and ion interactions. What is particularly interesting in the research study is the significant differences associated with the way the water reacts to multiple surfaces, which evidences that the dielectric reactions depending on the interface attributes are not trivial and should be taken into account. The results may be crucial in coming up with graphene coating or treating it in such a way that it is compatible with liquid exposures and increase the range of its functions in sensors and electronic devices where the count of liquid interactions plays a substantial role. Along the line of the consideration of the role of the defects in graphene itself, Klein et al. offer evidence to support the idea of how topological StoneWales defects are capable of promoting bonding and electronic coupling at the interface between graphene and metal. As they find, the existence of the defects in the theoretical models may not be considered, which may provide incomplete comprehension of the electronic dynamics at such interfaces. The study offers a fresh approach to design better-performing devices since, possibly by engineering such flaws, better electronic coupling can be achieved thereby leading to better interfacial quality on an overall basis at the metal-graphene interface.[32]

Table 1. Summary of Graphene Interface Studies and Key Findings

Interface Type	Materials Studied	Key Phenomena / Findings	Methods	Applications	Reference
Metal–Graphene	Graphene + Al, Ti	Oxide formation at the interface affects optical/electronic behavior	XPS, Raman spectroscopy	Transistors, optoelectronics	Wang et al.[29]
Electrochemical Metal–Graphene	Graphene-coated electrodes in electrolyte	Unique electrostatics influence charge storage & sensor response	Electrochemical modeling	Supercapacitors, sensors	Saraf et al.[30]
Defective Metal–Graphene	Graphene with Stone-Wales defects	Defects enhance bonding and charge transport at metal interface	DFT simulations, interface modeling	Nanoelectronics, spintronic layers	Klein et al.[32]
Dielectric–Graphene	Graphene on SiO_2, h-BN, van der Waals materials	Substrate selection influences mobility, dielectric screening and power efficiency	Transport measurements, dielectric analysis	FETs, low-power devices	Zhang et al.[33]

Dielectric-Aqueous-Graphene	Graphene-water interface with metallic/rigid surfaces	Water structure and ion response differ across rigid and metallic substrates	Molecular dynamics, electrostatic potential	Coatings, sensors	Loche et al.[31]
Sulfur-doped GO Interfaces	Graphene oxide + sulfur compounds	NDR and charge transfer behavior at functional interfaces	I-V curves, structural analysis	Diodes, memory elements	Figarova et al.[34] Abaszade et al.[35]

This may radically change the design of the next-generation nanoelectronic devices in which the efficient charge transport is crucial. Finally, Zhang et al. probe the influence of the effect substrates on the carrier mobility of graphene, urging the role of two-dimensional van der Waals dielectric materials as modifiers in the interface. It is through this study that a route to optimize the behaviour of devices by engineering the intrinsic characteristics of graphene by appropriate choice of interface materials would be made.[33] With their findings, they are able to explore the way to minimize the power consumption in the graphene-based devices, which are becoming overly critical in the regards of the contemporary electronic technologies in which the energy efficiency is a pressing need. To sum it up, all different types of interfaces with graphene, whether made of metal, dielectric, or polymer, present a range of problems and opportunities that should be explored to a significant extent. The differing characteristics of each type of interface portray a distinct interdependency of physical processes through which performance of tools dependent on the exceptional attributes of graphene could be improved. The significance of interdisciplinarity of this study requires the collaborative work between materials science, physics and engineering that helps to take full advantages of graphene in technological applications (table 1).

Graphene-Metal Interface Engineering

The graphene-metal interface will become decisive to the electrical, thermal and structural properties of the graphene-based electronic and optoelectronic devices. The contact chemistry in the case of graphene under the interaction with metal electrodes determines the interacting charge carrier injection, contact resistance, and the Fermi level alignment. Two main forms of bonding are possible at this interface, physisorption (weak van der Waals binding e.g. with Gd, Au or Pt), chemisorption (strong covalent bonding e.g. with Gd, Ni or Co), and they severely influence electronic coupling. Metals physisorbed are likely to conserve the band structure of graphene whereas chemisorbed metals may alter the Dirac cone creating changes in bandgap or a charge transfer effect. The difference in the work functions of graphene and the contacting metal sets the Schottky barrier height that is controllable by as doping or electrostatic gating. Surface cleaning, thermal annealing and interface functionalization are eventually used to reduce contact resistance and enhance carrier injection to accomplish this. Such refined techniques as edge-contacted geometry and intercalation of metals have been found to perform tremendously well electrically than traditional top-contact configurations. Also, the interface buffer layer of 2D materials such as hexagonal boron nitride (h-BN) is used in order to minimize the effect of metal-induced doping and retain the original properties of the graphene. Contact uniformity and reliability can further be enhanced by molecular doping or engineering of metal deposition processes (e.g. e-beam evaporation, sputtering), in which deposition is accomplished under ultra-high vacuum. In general, the semi precise engineering of graphene-metal interface is of vital importance to achieve low power, high speed and scalable graphene electronics. Avoiding the interaction of graphene with other substrates is important, and therefore, great interface engineering methods are needed. It is found that gadolinium-doped carbon nanotubes

and graphene oxide interfaces can be optimized in terms of electron transport under structural adjustments.[36] These results also prove that surface functionalization and nanostructure engineering are important in high-performance and stable interface in graphene-based devices. Graphene and its various applications in diverse applications like electronic and thermal management gadgets have put the field of graphene and metal interface engineering under intense scrutiny in the recent past. The key to the performance of graphene-based devices is the coupling of graphene and metal contacts that not only affects the electronic properties like contact resistance but also thermal performance like thermal conductivity and ability to dissipate heat at high frequencies. These interfaces are important in nanoelectronics since a deep grasp of their features is essential to be able to realize the full potential of graphene. In order to investigate the steps that could be taken to improve the electricity and thermal connection between graphene metal contact, different junction geometries have been tested out. Ohno et al.[37] differentiated between the two types of contacts (surface and edge) on graphene-metal interfaces and claimed that edge-contacted interfaces show significantly different contact resistances in comparison to surface-contacted interfaces, because of the bonding distance. This realization presents opportunities of radical design approaches in graphene devices where one can consider edge contact in reducing resistivity, and in a sense, overall device characteristics. In continuation of the reports on contact resistance reports, Zhai et al.[38] ventured into the study of the thermophysical process of thermal transport at two-dimensional interfaces, noting that the role of recognizing the electronic and phononic properties of thermal transport could not be overstated between such systems. Their results support the earlier study of the concept of interface thermal conductance (ITC) in metal-graphene systems in that the thermal effects between the metal especially by electrical means do not play much role in the overall performance of thermal transport at these interfaces. This explanation reiterates the dominance of phononic transport in such cases and it is thus important to optimize the thermal coupling options. Conclusively, the engineering of graphene-metal interface is a complex issue that incorporates thermal and electronic rationales. All these studies emphasize the relevance of interface properties, with new geometrical strategies like edge contacts and deployment of alloys with materials and methodologies becoming of importance to ensure improvement of device performance. Further studies that are required in this field should enable the creation of high-efficiency graphene-based electronics that would serve the growing requirements in contemporary technologies.

Graphene–Dielectric Interface Stability

The possible application is that the graphene-dielectric interface is essential in ensuring reliable performance of field-effect transistors (FETs), capacitors, sensors and other electronics devices. Subsequent to this interface, a number of thematics occur based on the roughness of the surface, charges trapped in the surface, dipole-formation, and remote phonons scattering, which have the capability of lowering the mobility of carriers in graphene. Common dielectrics include silicon dioxide (SiO2), aluminum oxide (Al2O3) and hafnium oxide (HfO2) and the dielectric elements create surface imperfection and charge traps that are incompatible with graphene. Charges trapped on the dielectric surface may result in potential hysteresis and Dirac point shift in the graphene which results to unreliable switching behavior and bias stress instability. Stability of the interface is enhanced by means such as atomic layer deposition (ALD), typically with prior seeding layers or surface functionalization (e.g. with NO2 or polymers) in order to guarantee uniform growth of the dielectric. Hexagonal boron nitride (h-BN), a chemically inert and atomically flat 2D dielectric material, makes a perfect and ideal substrate, because it acts as a minimal charge scattering substrate, and also retains the high mobility and the structural integrity of graphene. Thermal annealing, chemical passivation and self-

assembled monolayers (SAMs) are interfacial engineering methods that have proved useful in defect reduction and dielectric compatibility. Delamination or cracking due to mechanical strain and temperature difference mismatch between the dielectric and graphene is also possible and therefore the material selection and device architecture should have these effects in mind. Also, the environmental stability (e.g., Not affected by humidity, change of temperature) can also be made better by encapsulation using stable dielectric materials or multilayer passivation. Effective graphene-dielectric junction design guarantees predictable device functioning, high carrier electron mobility and a long life time of devices in high end electronic devices.

Contact resistance is also very important in determination of the efficiency of electron transport at the graphene-metal interface. The fact that the negative differential resistance (NDR) in the structures of sulfur-grafted graphene oxide was observed also indicates the quantum transport capability of this interface.[34] Gadolinium doping is one of the new technologies that are successful in the improvement of interfacial compatibility and the attainment of stable low-resistance graphene-metals contacts.[35] It is impossible to overestimate the role of interfacial bonding to enhance the strength of the graphene-dielectric interface. As an example, research articles have found that when a low-dielectric constant surface, e.g., self-assembled peptides is placed on graphene, the capacitive sensing performance improves significantly with increased interface bonding and does not sacrifice the dynamic performance of the material.[39] This is important as this will make the entire structure more stable and able to transfer the energy easily across the interface and this becomes significant especially in case of applications such as flexible electronics where mechanical strain cannot be avoided. As an example, growth of the particle size in the polymer network was found to be associated with enhanced thermal energy dissipation in the graphene to dielectric interface, which directly establishes the interface stability with the mechanical qualities in the composite material. This concept is important to explain why graphene properties are not the only features that define the thermal and mechanical stabilities but the dielectric composition of the composite.[40] An interfacial property can also be enhanced through the bond between nanostructured materials in the polymer matrices e.g. by the addition of layered double hydroxides (LDH) and graphene in polyvinyl alcohol (PVA) composites. The entire dielectric constant of the composite is also naturally higher as a result of the artificial increase in polarization at the interface, and this lowers the polarization effect of the graphene-dielectric interface through the addition of more electric dipoles per unit volume. The development of more polar interactions at the interface and the modified dielectric characteristics attains the importance of the design of the composites in producing stable and reliable graphene interfaces. In short, it can be seen that to stabilize the graphene-dielectric interface, a multi-pronged strategy needs to be adopted that includes enhancement of material properties, enhancement of interfacial bonding, fine tuning of fabrication process, and role of environmental factors at the interface needs to be understood comprehensively. The future of very stable and useful graphene-dielectrics composites is being pushed towards reality with emergent new methodologies and materials innovations, the next frontier in electronic uses. Summing up, the combination of many factors, both interrelated and unrelated, defines the stability at the graphene-dielectric interface, which depends on properties of a dielectric material, subsequent manufacturing techniques, and environmental factors. Further interdisciplinary research between materials scientists, physicists and engineers will be required to tease out the mysteries of these interfaces. It is only in such combined effort that gains can be achieved towards sustainable and reliable high-performance electronic applications.

Graphene-Polymer/Organic Interface Engineering

Interfaces graphene or polymeric or organic materials lie at the core of applications in

flexible electronics, biosensors, composite and energy devices. To maximize adhesion, charge transfer, dispersion and mechanical matching of the two elements, graphene is sought to be improved along with polymer via graphene-polymer interface engineering. The almost smooth, hydrophobic surface and robust 1pi -1pi interactions of pristine graphene frequently exhibit unfavorable interfacial binding with polar polymers, wherein surface modification is required. In the field of material science, specifically in the engineering process of graphene-polymer interface, significant developments have been made in terms of the analysis as well as maximization of the interactions that take place at the atomic and molecular scale. Graphene, which is a two-dimensional material that is renowned to possess exceptional mechanical, electrical, and thermal conductivity, has been used as a flexible medium in the combination with polymer in order to develop high-tech materials that can be utilized in a variety of industries such as in the electronics, sensor, and nanocomposites domains. The significant direction of the further improvement of the performance of graphene-based composite materials is the understanding of the nature of the interaction of graphene and polymers and the capabilities of these interactions to fine-tune the adhesion properties and mechanical stability of composite materials. Electronic properties of interface of graphene and dielectric materials affect stability and performance of electronic devices directly and especially because of trapped surface charges. EPR spectroscopy on the gadolinium-doped graphene oxide produced provides the information on the spin states and charge carriers reactivity in an interfacial environment. [36] These studies reveal that dielectric-graphene interfaces are stabilizable such that they can be utilized in energy efficient and long-lasting nano dimension electronics. Graphene surfaces can be seen to have defect engineering come up as one of the workable solutions in greatly improving the adhesion at the interface when graphene is used with polymers. Kumral et al.[41] tested the adhesion energy of pristine graphene through experiments, reporting a value of 7 mJ/m 2 when bonded to polydimethylsiloxane (PDMS), whereas defect engineering could increase the value of the adhesion energy to about 38 mJ/m2. The changes in adhesion with functionalized graphene reflect the effects of the heterogeneity of defect-engineered interfaces, making it apparent that optimizing interface design to a particular application need employ a customized interface design. The high adhesion energies may be converted into a better resistance to dynamic failures of graphene-based composites subjected to mechanical stress, which is of essence to life and stability in real settings. Also, the importance of interfacial mechanical properties in composites could be evidenced with the help of the study of Zhang and Yi-Long which examines the mechanical behavior at the interface of graphene and titanium with the help of computational modelling. They demonstrate the intricate dynamics of such a multilayer interface, using simulation to forecast the mechanical benefits maintained at nanoscale interfaces, which gives the needed understanding to the design of superior performing composite materials.[33] These kinds of simulations can be used to predict and evaluate mechanical integrity of composite systems, which translates into better methods of interface design which are elastic to different stresses. To sum up, the detailed discussion of graphene-polymer interface engineering allowed disclosing a complex view of the improvement of relationships between the capability and applicability of the graphene-based materials. Recent developments in material research through interfacial adhesion, van der Waals force exploitation, and the development of new surface modification techniques will culminate in far-reaching implications in a number of high-technology applications. Further months of both intra-disciplinary and inter-disciplinary research will become essential in the efforts to extend the limits of just what is possible with graphene-polymer composite materials to keep them aligned with the high-performance standards of contemporary technology.

Emerging Applications Requiring Interface Control

The graphene-polymer or organic interface is influential to the growth of hybrid flexible and biocompatible devices. Hydrophobic and Hydrophilic reactions of nanostructure surfaces are the major factors of mechanical fit and electrical match.[42] These interfacial characteristics lay the basis of maximizing the strength and performance of the graphene-polymer composites in real life. The interface control field is one which is fast changing requiring the investigation of new applications that go beyond existing paradigm of interaction. Conventional human-computer interaction (HCI) design methods, whose principle is largely based in desktop contexts, have been revealed as unsatisfactory in accommodating the modern mobile and cloud-based applications. Mohammed and Karagoylulu explain that the design principles of the standard HCI focus on task design, needs of the users, as well as functionality of systems do not fit the dynamic nature of mobile applications, which allows location-based services. Based on their results, M. Mohammed[43] propose the idea that established paradigms employed in desktop interface design no longer work in a mobile environment and there is an urgent need to adjust HCI framework in tandem with the rise of technologies.[43] Computing Bujack et al.[44] describe the Simplified Interface to Complex Memories (SICM) of the Exascale Computing Project that offers solutions to the issue of controlling complex memory hierarchies. The project can provide better control and configurability of the different memory technologies by the establishment of standard interfaces that enable discovery and sharing of data. This is an innovation that plays a key role in enabling the performance trade-offs that are necessary in high-performance computing applications, which are further challenging the significance of sufficient interface control in the emerging computing environments.

Energy storage and conversion (e.g., supercapacitors, batteries)

Nanomaterials of graphene have become popular applications in energy storage and conversion devices and interface engineering plays an important role in the manipulation of ion mobility as well as electronic conductivity. The results of the research of gadolinium-doped carbon nanotubes and functionalized graphene structures show improvements in thermal and electrochemical characteristics of such materials in supercharging cap and battery electrode design. Moreover, the synergistic effect between graphene and MXenes emphasizes the corresponding principle of the stable interfacial design in enhancing the capacitance and cycling performance.[45] Graphene in materials has been found to be a possible component of an energy storage and energy conversion system for its superior electrical conductivity, a large surface area, and chemical tunability. Graphene is a good electrode material in supercapacitors that permits rapid charging discharging processes and high-power density by electric double-layer capacitance and pseudo capacitance capabilities. Composite electrodes may include Graphene oxide (GO) and reduced graphene oxide (rGO) to enhance ion accessibility and structural stability, commonly as a combination with conducting polymers or metal oxides. Graphene-based 3D formation (aerogel, foams) has the advantages of improving electrolyte diffusion characteristics and supporting mechanical stiffness, which is very critical to flexible and wearable energy applications.

Graphene is used as a conductive additive or active material in anode and cathode of the lithium-ion batteries (LIBs) to improve electron transport and provide cycling volume buffer. Within anodes, a graphene silicon compound is especially promising, because the graphene component can absorb the silicon as it swells up, prevent the formation of cracks, and effectively maintain the structural integrity of the compound. In the case of metal air batteries, catalysts of graphene materials have been used as economically viable and long-lasting replacements of precious metals such as Pt or Ir to enhance oxygen reduction and oxygen evolution reaction (ORR/OER). Graphene disperses catalytic nano-particles in fuel cell, enhances durability and

facilitates the transport of protons or electrons (depending on functionalization). The contact between graphene and electrolytes (liquid, solid or gel) should also be engineered to both drive ion transfer and reduce side reactions and improve device durability. Altogether, the energy storage and conversion systems incorporating interface-engineered graphene produce better performance parameters, e.g., capacity, cycle life, energy density, preparing the ground of a next-generation sustainable power technology.[46,47,48]

Graphene-based quantum devices

The peculiarities of the electronic characteristics of graphene, massless Dirac fermion and a high carrier mobility, create an excellent marriage of opportunities to develop a completely new generation of quantum devices. The atomically thin and two-dimensional property enables it to exhibit unprecedented control over the charge transport, spin, and the valley degrees of freedom, which are the building blocks of the quantum information processing. GQDs which effectively trap charge carriers on a nanoscale volume, have a discrete energy structure and quantum confinement effects which presently find application in single-electron transistors and quantum sensors. Twisted bi-layer graphene at the socalled magic angle exhibits moirre superlattice effects resulting in correlated electron behavior and superconductivity and is a frontier material enabling quantum simulation. Josephson junctions Graphene-based Josephson junctions, where graphene is inserted between superconducting contacts, exhibit coherent quantum transport and may be applicable in superconducting qubits. Graphene has a high carrier mobility, spin coherence and band-structure tunability that is valuable in the endeavor of integrating it in quantum devices. The Gadolinium-doped carbon nanotubes have exhibited immense photoconductive properties and electron paramagnetic resonance technology, which is favorable in quantum transistors and single electron applications.[49,50] The present results are important to understanding how interface interactions can be customized to increase coherence and control in graphene-based quantum systems. In valleytronics, the unique K and K 0 valleys within momentum space in graphene can also be used as binary quantum states to encode and process information, and this represents a new avenue beyond charge-based computing.

Integration with CMOS technology

A major breakthrough towards scalable, high-performance and energy efficient electronic systems is by integrating graphene, with complementary metal-oxide semiconductor (CMOS). Due to its exceptional carrier mobility, thermal conductivity, and the flexability, graphene promises to be a hot candidate to break the performance barrier in traditional silicon-based CMOS. Graphene and CMOS combine to hold out the promise of high speed and low power electronic components, but this needs a strong thermal and structural integrity to be achieved at the interface. The conductive porous carbonates extracted by the biomass, e.g. hemp fibers, exhibit promising thermal control characteristics that can make it compatible with CMOS fabrication processes.[51] Further, electrochemically modified carbon materials of walnut shells emphasize the significance of a thermal activation and surface functionalization to be used in a large-scale setup.[52] Perhaps the biggest application is in high-speed field-effect transistors (FETs), where graphene in principle can be used as a channel material because of its ultrafast carrier dynamics and short gate delay. Nevertheless, graphene has a zero bandgap, which complicates its use in the digital logic; attempts to introduce a bandgap either by stacking in bilayer, fabricating nanoribbon, or engineering substrates are a vigorously investigated topic. Graphene also offers the potential of high-performance inter-connection material in CMOS circuits with reduced resistive losses and local heating in high density nanoscale structures.[53] Graphene has linear dispersion and much higher cut-off frequencies (>= 300 GHz) compared to silicon and therefore linear graphene may be used as a wideband amplifier, mixer or detector in analog and RF

(radio frequency) applications far beyond silicon. Even on the sensors area, GrapheneCMOS is promising, graphene can be used as an extremely sensitive active layer, and the CMOS platform offers an indispensable signal processing and data transmission infrastructure. However, Hybrid integration methods either involves CVD grown graphene transfer onto processed CMOS wafers or co fab using compatible material and processes.[54] The issues of thermal budget compatibility, interface contamination and area uniformity (large scale) have to be overcome to obtain an adequately reliable CMOS-graphene co-fabrication. Effective incorporation of graphene with CMOS based technology brings into ways multifunctional chips incorporating logic, memory, sensing, communication into one low powered and high-speed chip.

CONCLUSIONS

Briefly, this chapter has identified the intrinsic properties of graphene and put an emphasis on the crucial position of the interface engineering in realizing its full potential in a wide range of applications. In a careful systematic study of the interaction of graphene with different materials, i.e., metals, dielectrics and polymers, we have shown that the device stability, functional performance and charge transport depend directly on the quality of the interface. It was observed that the interface-specific tactics, chemical modification and structural optimization, can be discussed as good recommendations when it comes to enhancing compatibility and reliability in practical devices. Moreover, the recent developments of energy storage, quantum, and CMOS integration application show that precision interfacial control is essential to address the future technology requirements. As graphene as a material morphs further beyond a lab material to the heart of next-generation technology, its interfacial properties will be a critical parameter to introduce new generations of improvements in electronics, sensor and energy systems.

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